Abstracts

Planar Doped Barrier Mixer and Detector Diodes as Alternatives to Schottky Diodes for Both Microwave and Millimetre Wave Applications

I. Dale, A. Condie, S. Neylon and M.J. Kearney. "Planar Doped Barrier Mixer and Detector Diodes as Alternatives to Schottky Diodes for Both Microwave and Millimetre Wave Applications." 1989 MTT-S International Microwave Symposium Digest 89.1 (1989 Vol. I [MWSYM]): 467-470.

Planar Doped Barrier diodes with extremely low barrier heights and highly asymmetric I-V characteristics have been developed using MBE grown GaAs material. This paper reports upon the RF performance of these devices and discusses the significant advantages offered by PDB devices over conventional Schottky diodes for mixer and detector applications at both microwave and millimetre wave frequencies.

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